# BTA216X series B

### **GENERAL DESCRIPTION**

Glass passivated high commutation triacs in a full pack, plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

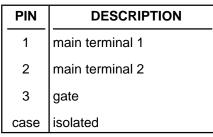
### PINNING - SOT186A

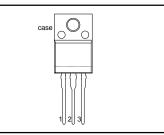
## QUICK REFERENCE DATA

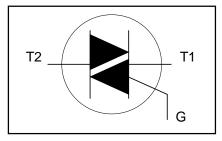
SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BTA216X-	500B	600B	800B	
V <sub>DRM</sub>	Repetitive peak off-state	500	600	800	V
	voltages				
I <sub>T(RMS)</sub>	RMS on-state current	16	16	16	A
I <sub>TSM</sub>	Non-repetitive peak on-state current	140	140	140	A

### PIN CONFIGURATION

### SYMBOL







### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V <sub>drm</sub>	Repetitive peak off-state voltages		-	<b>-500</b> 500 <sup>1</sup>	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave;	-		16		A
I <sub>TSM</sub>	Non-repetitive peak on-state current	$T_{hs} \le 38 \ ^{\circ}C$ full sine wave; $T_j = 25 \ ^{\circ}C$ prior to surge t = 20 ms	_		140		A
		t = 16.7 ms	-		150		
l²t dI <sub>T</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after triggering		-		98 100		A <sup>2</sup> s A/μs
$\begin{matrix} I_{GM} \\ V_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms	- - -		2 5 5 0.5		A V W W
T <sub>stg</sub> T <sub>j</sub>	Storage temperature Operating junction temperature	period	-40 -		150 125		ů Ú

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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### **ISOLATION LIMITING VALUE & CHARACTERISTIC**

 $T_{hs} = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>isol</sub>	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65% ; clean and dustfree	-		2500	V
C <sub>isol</sub>	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-hs</sub> R <sub>th j-a</sub>	Thermal resistance junction to heatsink Thermal resistance junction to ambient	full or half cycle with heatsink compound without heatsink compound in free air		- - 55	4.0 5.5 -	K/W K/W K/W

### STATIC CHARACTERISTICS

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$					
01		T2+	+ G+	2	18	50	mA
		T2+	+ G-	2	21	50	mA
		T2-	- G-	2	34	50	mA
$I_{L}$	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$					
-		T2+	+ G+	-	31	60	mA
		T2+	+ G-	-	34	90	mA
		T2-	- G-	-	30	60	mA
I <sub>H</sub>	Holding current	$V_{\rm D} = 12 \text{ V}; \text{ I}_{\rm GT} = 0.1 \text{ A}$		-	31	60	mA
ι <sub>н</sub> V <sub>T</sub>	On-state voltage	$I_{T} = 20 \text{ A}$		-	1.2	1.5	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{\rm D} = 12 \text{ V}; \text{ I}_{\rm T} = 0.1 \text{ A}$		-	0.7	1.5	V
		$V_{\rm D} = 400 \text{ V}; I_{\rm T} = 0.1 \text{ A}; T_{\rm i} = 125 \text{ °C}$		0.25	0.4	-	V
I <sub>D</sub>	Off-state leakage current	$V_{D}^{D} = V_{DRM(max)}; T_{j} = 125 °C$		-	0.1	0.5	mA

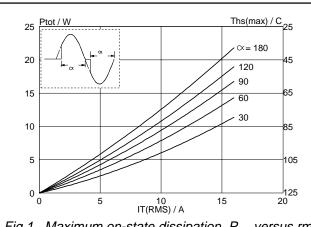
#### **DYNAMIC CHARACTERISTICS**

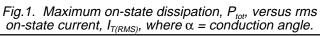
 $T_i = 25$  °C unless otherwise stated

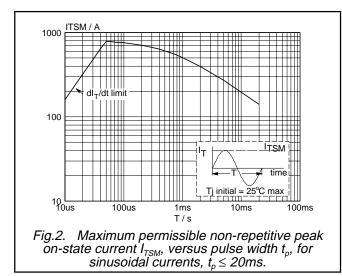
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/µs
dl <sub>com</sub> /dt	off-state voltage Critical rate of change of commutating current	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}; \text{ T}_{j} = 125 \text{ °C}; \text{ I}_{T(RMS)} = 16 \text{ A};$ without snubber; gate open circuit	-	28	-	A/ms
t <sub>gt</sub>		$I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

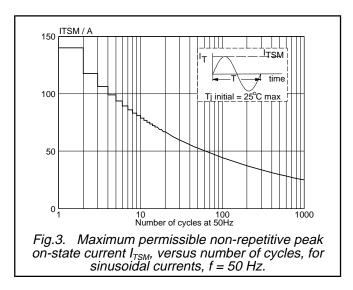
<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

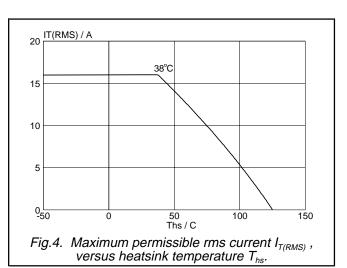
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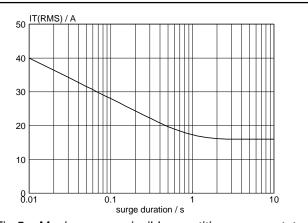
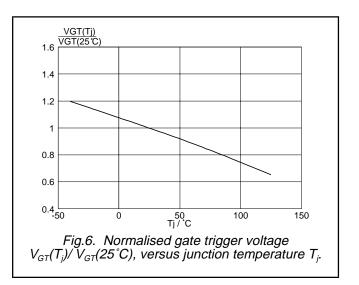
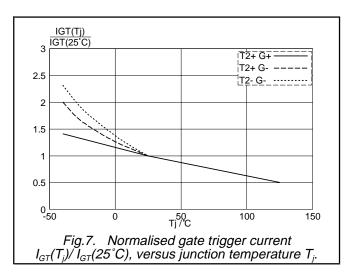
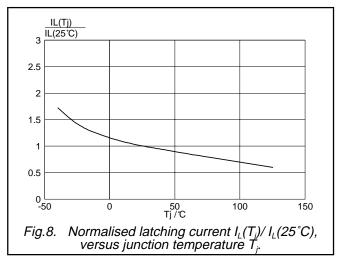


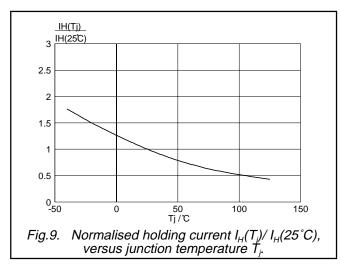
Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{hs} \le 38$  °C.

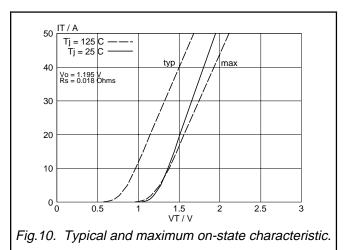


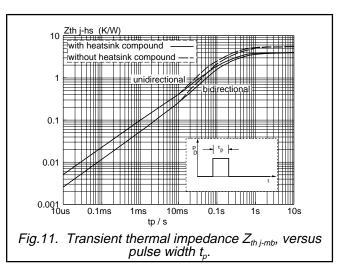
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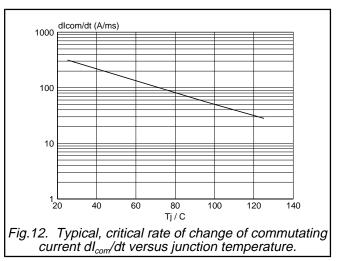








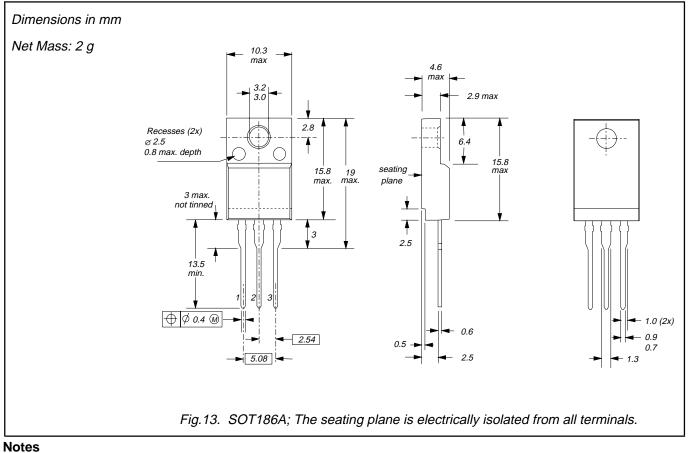




#### Product specification

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## **MECHANICAL DATA**



Refer to mounting instructions for F-pack envelopes.
Epoxy meets UL94 V0 at 1/8".

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### DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				
Where application information is given, it is advisory and does not form part of the specification.				
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